

# Lesson 23: Introduction to Solar Energy and Photo Cells

ET 332a

Dc Motors, Generators and Energy Conversion Devices

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1

## Learning Objectives

After this presentation you will be able to:

- Identify the solar spectrum
- Determine the angle that captures the maximum solar energy
- Explain the atomic difference between conductor, insulators, and semiconductors
- Explain physics behind the photoelectric effect
- Compute the open circuit voltage and short circuit current of a photocell

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2

## Solar Energy and Photocells

### Solar Spectrum

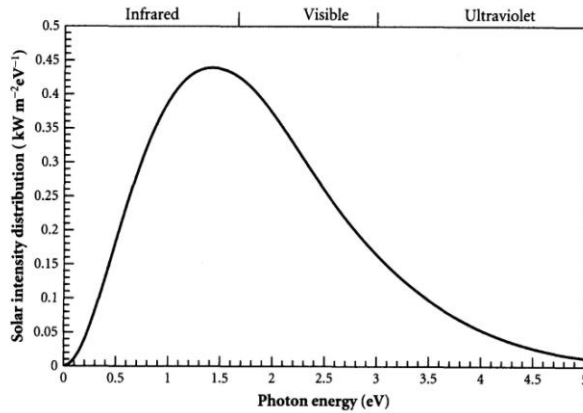


Fig. 6.1 Black-body spectrum at  $T = 5800$  K. The total intensity is normalized to that of the AM1.5 solar spectrum of  $1 \text{ kW m}^{-2}$ .

AM0 =  $1.36 \text{ kW/m}^2$   
Incident on  
Atmosphere

AM1.5-  $1.0 \text{ kW/m}^2$   
Passing through  
Atmosphere

Incident to  $48^\circ$  angle  
to vertical

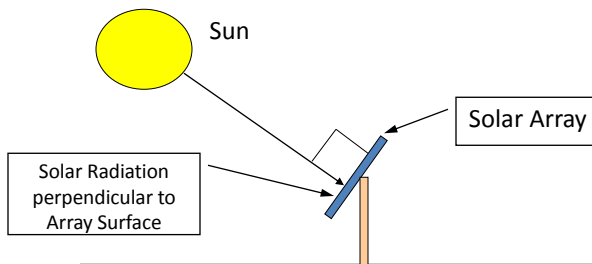
Includes absorption  
of water vapor,  $\text{CO}_2$ ,  
methane.

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3

## Solar Energy Conversion

**Direct Radiation** depends on season, location, cloudiness. Yearly average 30%  
Average Intensity ( $\text{W/m}^2$ ) 10% in lower Canada to 50% in  
tropics



**Diffuse Radiation** unfocusable. Long wavelengths scatter more color sky blue.

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4

## Solar Intensity

Example: Direct sunlight with an average intensity of  $450 \text{ W/m}^2$  is incident perpendicularly to a solar cell. The cell has an area of  $0.15 \text{ m}^2$ . Calculate to total incident energy on the cell for one day in kWh. What is the percentage energy reduction if the sunlight falls on the cell at  $35$  degrees from perpendicular?

$$I := 450 \cdot \text{W} \cdot \text{m}^{-2} \quad \text{Incident solar energy}$$

$$A := 0.15 \cdot \text{m}^2 \quad \text{Solar cell area}$$

$$P := I \cdot A \quad P = 67.5 \text{ W}$$

Power multiplied by time gives energy

$$t := 24 \cdot \text{hr}$$

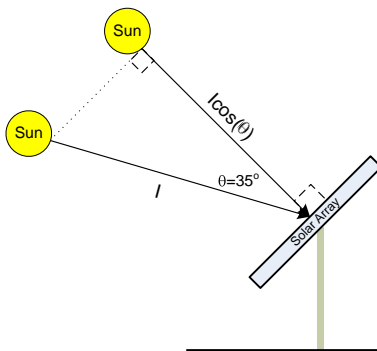
$$E := P \cdot t \quad E = 1620 \text{ W} \cdot \text{hr}$$

$$E \cdot \frac{1 \cdot \text{kWh}}{1000 \cdot \text{W} \cdot \text{hr}} = 1.62 \text{ kWh} \quad \text{Convert to Kilowatt-hours}$$

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5

## Solar Intensity



Example: cont.

$$\theta := 35 \cdot \text{deg}$$

$$P_{30} := I \cdot \cos(\theta) \cdot A \quad P_{30} = 55.3 \text{ W}$$

Power multiplied by time gives energy

$$t := 24 \cdot \text{hr}$$

$$E_{30} := P_{30} \cdot t \quad E_{30} = 1327 \text{ W} \cdot \text{hr}$$

$$E_{30} \cdot \frac{1 \cdot \text{kWh}}{1000 \cdot \text{W} \cdot \text{hr}} = 1.3 \text{ kWh} \quad \text{Convert to Kilowatt-hours}$$

$$\% \text{Reduction} := \left( \frac{E - E_{30}}{E} \right) \quad \% \text{Reduction} = 18.1\%$$

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6

## Conductors, Insulators and Semiconductors

Conductors – Free electrons in atomic structure

Valence electrons form current when electric potential applied.

Examples: copper, silver

Insulators – No free electrons in valence band

Examples: glass, plastics.

Semiconductors – Valence electrons exist

Bonded to other atoms

Bonds broken by external energy like heat or light

Examples: Silicon, Germanium

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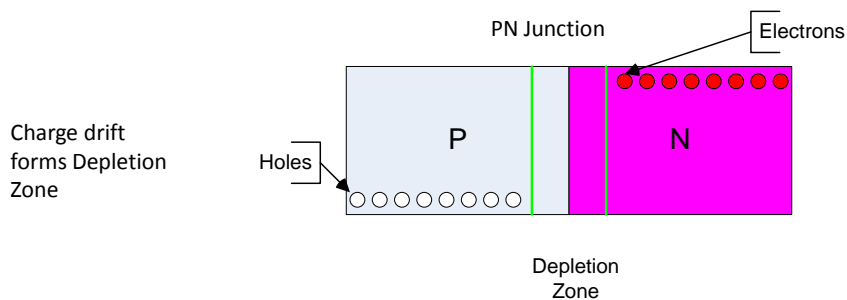
7

## Semiconductors

Doped Semiconductors – Impurities added to increase conductance

P-type semiconductor - excess holes (absent electrons)

N-type semiconductor – excess electrons



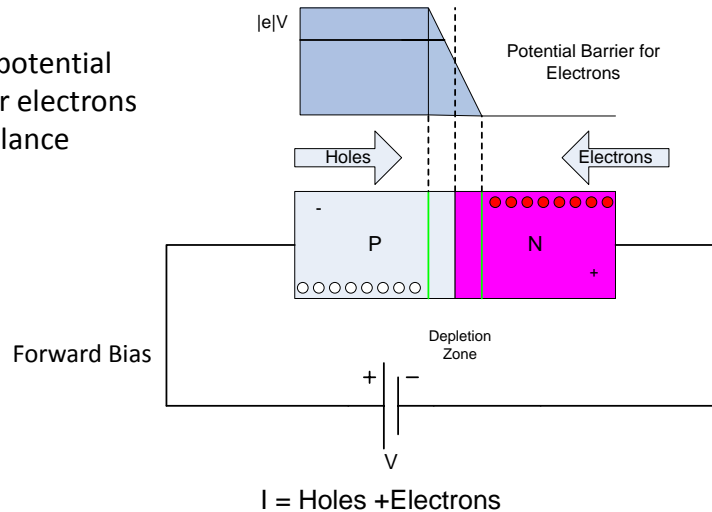
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8

## Forward Biased PN Junction

V lowers potential barrier for electrons  
upsets balance

I flows



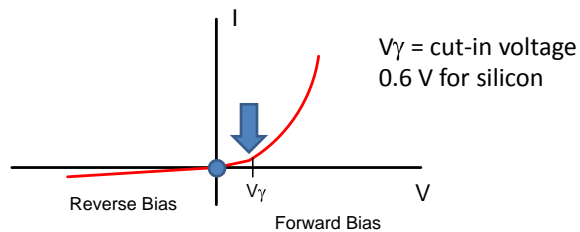
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9

## PN Junction-Diode Operation

### PN Junction Characteristic

Junction conducts  
when forward biased



$$I = I_s (e^{V/V_T} - 1)$$

$V_T = \text{Voltage-equivalent of Temperature} = 0.026 \text{ V at room temperature}$   
 $I_s = \text{saturation current depends on junction area and doping}$

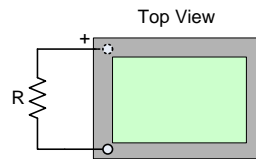
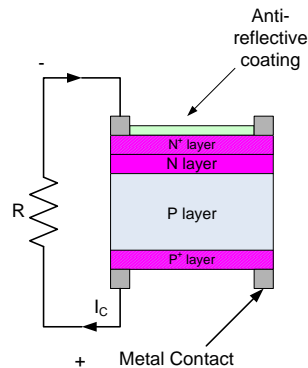
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10

## Photoelectric Effect

Light striking a PN junction creates currents. Photons must have sufficient energy increase electron energy and create Electron/hole pairs



Photon  $E > 1.1 \text{ eV}$

$$I_C = I_L - I_s \left( e^{\frac{I_C R}{V_T}} - 1 \right) = I_L - I_s \left( e^{\frac{V}{V_T}} - 1 \right)$$

$I_C$  = cell current

$I_L$  = reverse current

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11

## Open Circuit Voltage/Short Circuit Current

Open circuit means  $R = \infty$  and  $I_C = 0$ , so open circuit voltage is

$$V_{OC} = V_T \ln \left( 1 + \frac{I_L}{I_s} \right) \approx V_T \ln \left( \frac{I_L}{I_s} \right)$$

$V_T = 0.026 \text{ V}$  at room temperature

$I_s$  = saturation current

$I_L$  = reverse current

Cell power output given by

$$P_C = I_C V = I_C^2 R$$

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12

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## **END LESSON 23**